

Apple. No. 10/023,825  
Reply to Office action of 09/17/2003

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### **Listing of Claims:**

Claim 1. (cancelled).

Claim 2. (currently amended) The method of Claim 13, wherein said ~~masking material is~~ blocking layer comprises silicon nitride.

Claim 3. (currently amended) The method of Claim 13, wherein said sidewall spacers consist predominantly of silicon dioxide.

Claim 4. (currently amended) The method of Claim 13, wherein said patterned polysilicon layer is separated from said semiconductor substrate by a gate oxide layer.

Claims 5-12. (cancelled).

Claim 13. (new) A method of forming an integrated circuit, comprising the steps of:  
forming a polysilicon layer over a semiconductor substrate;  
forming a blocking layer over said polysilicon layer;  
patterning and etching said polysilicon layer and said blocking layer;  
then, implanting an initial dose of first conductivity type dopant to form source/drain extension regions in said semiconductor substrate;  
then, removing said blocking layer;  
forming sidewall spacers adjacent said polysilicon layer;  
then, implanting an additional dose of first conductivity type dopant to form main source/drain regions in said semiconductor substrate;  
then, depositing a metal layer and reacting said metal layer with portions of said polysilicon layer to form a conductive silicide.